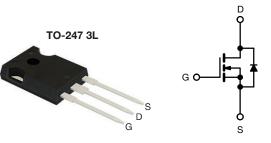


MaxSiC™ 1200 V N-Channel SiC MOSFET



N-Channel MOSFET

139

Single

Marking Code: 120A080FW

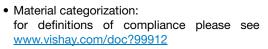
P_D (W)

Configuration

PRODUCT SUMMARY V_{DS} (V) at T_{J} max. 1200 $R_{DS(on)}$ typ. (mΩ) at 25 °C $V_{GS} = 20 \text{ V}$ 80 Q_g typ. (nC) 47.3 I_D (A) 29 C_{oss} typ. (pF) 50

FEATURES

- Fast switching speed
- Short circuit withstand time 3 µs





APPLICATIONS

- Charger
- · Auxiliary motor drive
- DC/DC converter

ORDERING INFORMATION	
Package	TO-247 3L
Lead (Pb)-free and halogen-free	MXP120A080FW-Y-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^{\circ}$	°C, unless otherwis	se noted)			
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage ^a		V_{DS}	1200	V	
Gate-source voltage		V_{GS}	-10 / +22	7 v	
Continuous drain current	T _C = 25 °C	I _D	29		
	T _C = 100 °C	I _D	18	Α	
Pulsed drain current ^b		I _{DM}	58		
Short-circuit withstand time		T _{SC}	3	μs	
Maniananananananalianiantian	T _C = 25 °C	P _D	139	W	
Maximum power dissipation	T _C = 100 °C	P_{D}	56] vv	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150	°C	
Soldering recommendations (peak temperature)	For 10 s		260	°C	

Notes

- a. $T_J = 25$ °C to 150 °C
- b. Repetitive rating; pulse width limited by maximum junction temperature



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THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	40	°C/W
Maximum junction-to-case (drain)	R_{thJC}	-	0.9	G/ VV

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static		^		•	•	•	
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_{D} = 1 \text{ mA}$		1200	-	-	V
Onto a summer thousand and unable and (Al)		$V_{DS} = V_{GS}$, $I_D = 5$ mA		-	2.69	-	V
Gate-source threshold voltage (N)	V _{GS(th)}	$V_{DS} = V_{GS}$	V _{DS} = V _{GS} , I _D = 5 mA, T _J = 150 °C		1.86	-	V
Gate-source leakage	1	V _{GS} = +22 V, V _{DS} = 0 V		-	-	100	nA
Gate-source leakage	I _{GSS}	V _{GS} =	V _{GS} = -10 V, V _{DS} = 0 V		-	-100	IIA
Zero gate voltage drain current	I _{DSS}	V _{DS} =	960 V, V _{GS} = 0 V	-	-	10	μΑ
		V _{GS}	$V_{GS} = 20 \text{ V}, I_D = 20 \text{ A}$		80	100	
Drain-source on-state resistance	P-ac	$V_{GS} = 20 \text{ V}$	V _{GS} = 20 V, I _D = 20 A, T _J = 150 °C		141	176	- mΩ
Dialii-Source oii-State resistance	R _{DS(on)}	V _{GS}	V _{GS} = 18 V, I _D = 20 A		99	124	
		V _{GS} = 18 V	, $I_D = 20 \text{ A}$, $T_J = 150 ^{\circ}\text{C}$	-	146	183	
Dynamic							
Input capacitance	C _{iss}		V _{GS} = 0 V, V _{DS} = 800 V, f = 1 MHz		1156	-	pF
Output capacitance	C _{oss}				50	-	
Reverse transfer capacitance	C _{rss}				5	-	
Coss Stored Energy	E _{oss}				10	-	μJ
Total gate charge	Q_g				47.3	-	
Gate-source charge	Q_{gs}	$V_{GS} = 18 \text{ V}$	$I_D = 20 \text{ A}, V_{DS} = 800 \text{ V}$	-	14.2	-	nC
Gate-drain charge	Q_{gd}			-	17.8	-	<u>l</u>
Gate Resistance	R_g	V _{DS} = 0 V, f = 1 MHz		-	9.8	-	Ω
Switching Characteristics							
Turn-on delay time	t _{d(on)}			-	25.6	-	
Rise time	t _r				15.6	-	ns
Turn-off delay time	t _{d(off)}	$V_{GS} = -5 \text{ V} \sim 18 \text{ V}, I_D = 20 \text{ A}, \\ V_{DS} = 800 \text{ V}, R_{g(ext)} = 4.4 \Omega$		-	16.0	-	113
Fall time	t _f			-	9.0	-	
Turn-on switching energy	E _{on}			-	386	-	μJ
Turn-off switching energy	E _{off}			-	37	-	μυ
Reverse Diode Characteristics							
Reverse recovery time	t _{rr}	V _{GS} = -5 V, I _{SD} = 20 A, V _R = 800 V, di/dt = 1000 A/μs		-	14	-	ns
Reverse recovery charge	Q _{rr}			-	35	-	nC
Reverse recovery current	I _{rrm}			-	4.5	-	Α

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

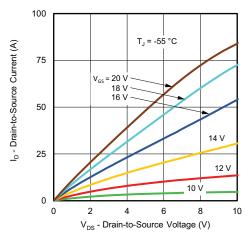


Fig. 1 - Typical Output Characteristics

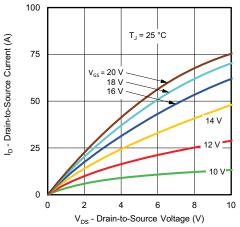


Fig. 2 - Typical Output Characteristics

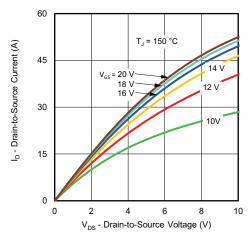


Fig. 3 - Typical Output Characteristics

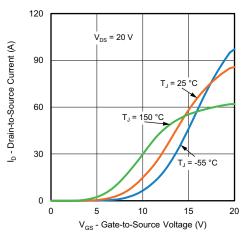


Fig. 4 - Typical Transfer Characteristics

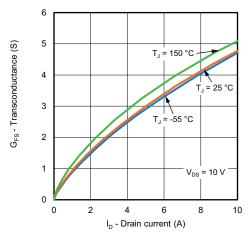


Fig. 5 - Forward Transconductance vs. Drain Current

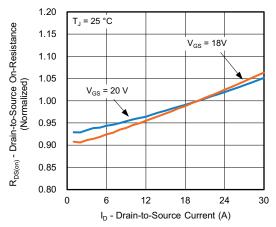


Fig. 6 - Normalized On-Resistance vs. Drain-to-Source Current



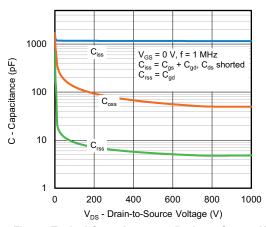


Fig. 7 - Typical Capacitance vs. Drain-to-Source Voltage

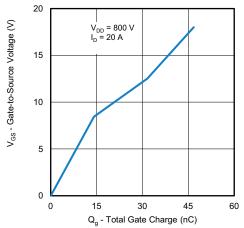


Fig. 8 - Typical Gate Charge vs. Gate-to-Source Voltage

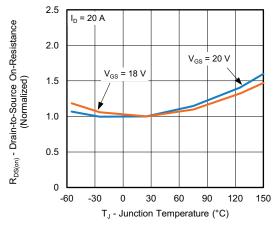


Fig. 9 - Normalized On-Resistance vs. Temperature

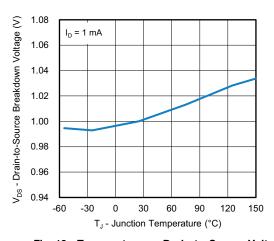


Fig. 10 - Temperature vs. Drain-to-Source Voltage

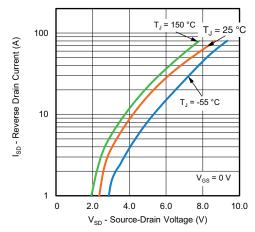


Fig. 11 - Typical Source-Drain Diode Forward Voltage

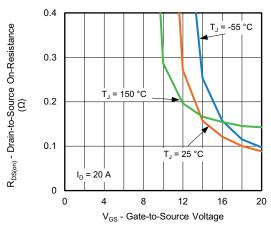


Fig. 12 - On-Resistance vs. Gate-to-Source Voltage

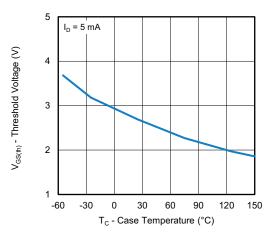


Fig. 13 - Threshold Voltage vs. Case Temperature

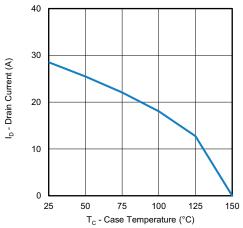


Fig. 14 - Drain Current vs. Case Temperature

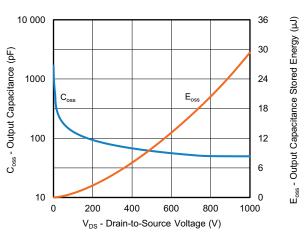


Fig. 15 - Output Capacitances and its Stored Energy vs.

Drain-to-Source Voltage

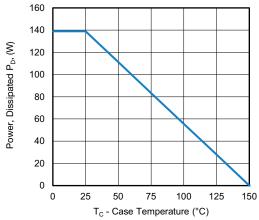


Fig. 16 - Power, Dissipated P_D vs. Case Temperature

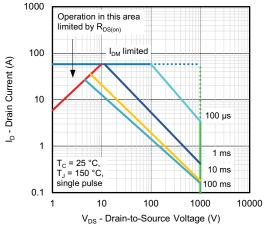


Fig. 17 - Safe Operating Area

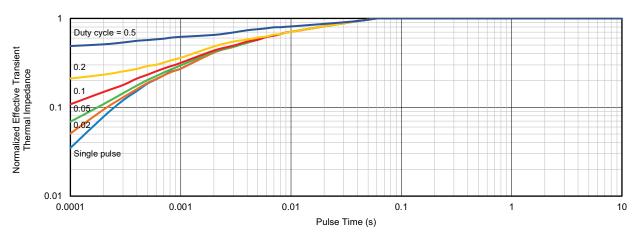


Fig. 18 - Normalized Effective Transient Thermal Impedance



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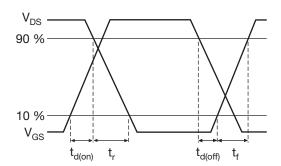


Fig. 19 - Waveforms of Switching Time

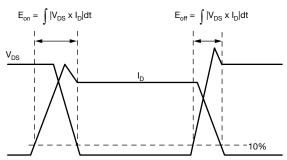


Fig. 20 - Waveforms for Switching Energy

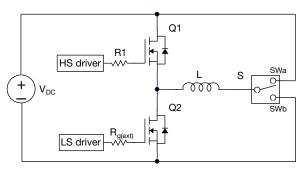


Fig. 21 - Switching and Reverse Diode Characteristics Measurement Circuit

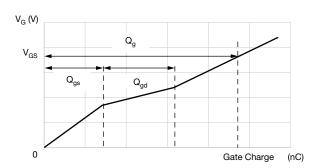


Fig. 22 - Waveforms for Gate Charge

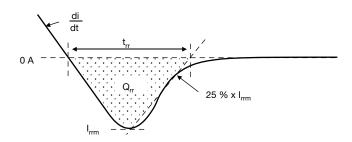


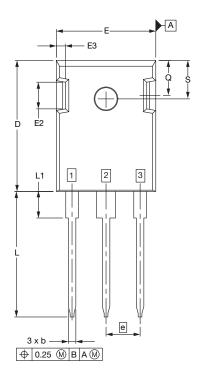
Fig. 23 - Waveforms for Reverse Recovery

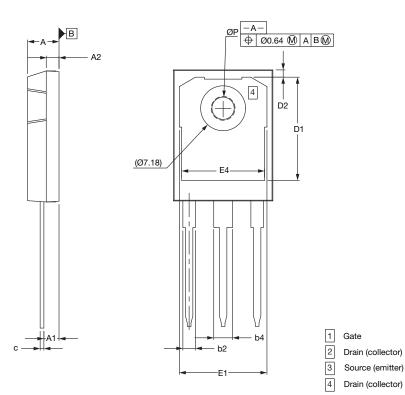
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Case Outline for TO-247AD 3L

FACILITY CODE: N





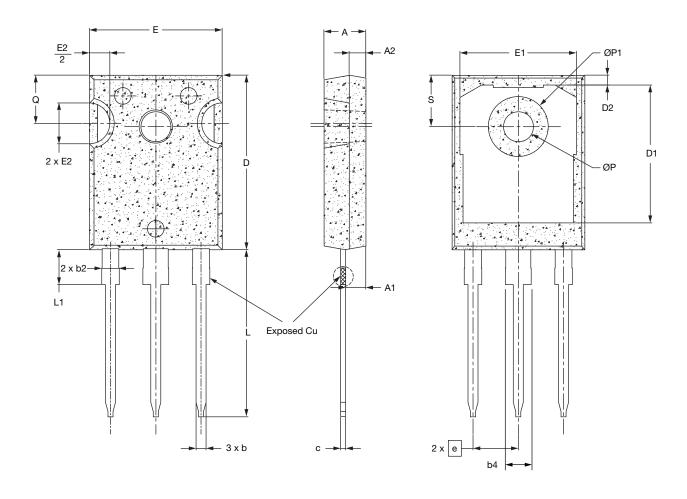
DIM.	MILLIM	ETERS
DIIVI.	MIN.	MAX.
A	4.83	5.21
A1	2.29	2.54
A2	1.91	2.16
b	1.07	1.33
b2	1.91	2.41
b4	2.87	3.38
С	0.55	0.68
D	20.80	21.10
D1	16.25	17.65
D2	0.95	1.25
Е	15.75	16.13
E1	13.10	14.15
E2	3.68	5.10
E3	1.00	1.90
E4	12.38	13.43
е	5.44	BSC.
N	3	3
L	19.81	20.32
L1	4.10	4.40
ØP	3.51	3.65
Q	5.49	6.00
S	6.04	6.30

Notes

- All metal surfaces: tin plated (MATTE), except area of cut Dimensioning and toleranceing confirm to ASME Y14.5M-1994
- All dimensions are in millimeters
- This drawing will meet all dimensions requirement of JEDEC outlines TO-247 AD



FACILITY CODE: 9







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DIM	MILLIMETERS			
DIM.	MIN.	NOM.	MAX.	
Α	4.83	5.02	5.21	
A1	2.29	2.41	2.55	
A2	1.50	2.00	2.49	
b	1.12	1.20	1.33	
b2 ⁽¹⁾	1.91	2.00	2.39	
b4 ⁽¹⁾	2.87	3.00	3.22	
С	0.55	0.60	0.69	
D (2)	20.80	20.95	21.10	
D1 ⁽³⁾	16.25	16.55	17.65	
D2	0.51	1.19	1.35	
E (2)	15.75	15.94	16.13	
E1 ⁽³⁾	13.46	14.02	14.16	
E2	4.32	4.91	5.49	
е	5.44 BSC.			
L	19.81	20.07	20.32	
L1 ⁽⁴⁾	4.10	4.19	4.40	
ØP ⁽⁵⁾	3.56	3.61	3.65	
ØP1	7.19 ref.			
Q	5.39	5.79	6.20	
S	6.04	6.17	6.30	
ECNI E24 0220 Pay A 12 May 200	24	•		

ECN: E24-0229-Rev. A, 13-May-2024

DWG: 6118

Notes

- Package reference: JEDEC TO-247, variation AD
- All dimensions are in mm
- Slot required, notch may be rounded
- (1) Dimension b2 and b4 does not include dambar protrusion
- (2) Dimension D and E do not include mold flash
- (3) Thermal pad contour optional within dimension D1 and E1
- (4) Lead Finish Uncontrolled In L1
- $^{(5)}$ ØP to have a draft angle of 1.5 $^{\circ}$ ref. to the top of the part with hole diameter of 3.91mm



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